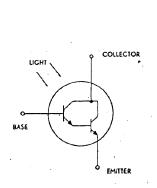
MAL11 MAL12

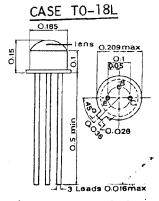
NPN

SILICON PHOTO

DARLINGTON TRANSISTORS

The MAL11, MAL12 are NPN silicon photo darlington transistors for use in sensitive photo detector circuits. They are supplied in selected light current groups.





All dimensions in inches

ABSOLUTE MAXIMUM RATINGS
Collector-Emitter Voltage
Emitter-Collector Voltage
Collector Current
Total Power Dissipation (TA \leq 25°C)
Operating Junction & Storage Temperature

VCEO
VECO
I_{C}
Ptot
T_{j} , T_{stg}

With difficultions in	III CITES
MAL11	MAL12
30V	25V
5V	
100m A	
300mW	
-55 to +1	00°C

ELECTRICAL CHARACTERISTICS (TA=25°C)

PARAMETER	SYMBOL	MAL11 MIN TYP MAX	MAL12 MIN TYP MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	LVCEO*	30 50	25 40	٧	IC=10mA (Pulsed) IB=0
Emitter-Collector Breakdown Voltage	BVECO*	5 8.5	5 8.5	V	IE=0.1mA IB=0
Collector Cutoff Current (Dark current)	ICEO*	0.2	0.5	μА	VCE=5V IB=0
Light Current Group A Group B Group C Group D		0.5 1 2 1 2 4 3 5 10	1 2 4 3 5 10 7 12 20	mA mA mA	VCE=3V H=2mW/cm ²

^{*} Tested in complete darkness.

^{**} The light current is the collector to emitter current measured at specified irradiance (H). The radiation source is an unfiltered tungsten filament lamp at 2874 K color etmperature.

TYPICAL CHARACTERISTICS AT TA=25°C

SWITCHING TIME

